Mircea D Guina

List of Publications by Year in Descending Order

345 papers	3,941 citations	30 h-index	41 g-index
468 ext. papers	4,896 ext. citations	3.1 avg, IF	5.35 L-index

#	Paper	IF	Citations
345	Thermal behavior and power scaling potential of membrane external-cavity surface-emitting lasers (MECSELs). *IEEE Journal of Quantum Electronics*, **2022**, 1-1	2	1
344	Polarized spectroscopy and SESAM mode-locking of Tm,Ho:CALGO.. *Optics Express*, **2022**, 30, 7883-7893	3.3	2
343	Bandgap energy model for GaInNAsSb/GaAs alloys with high N content and strain influence. *Journal of Crystal Growth*, **2022**, 584, 126574	1.6	0
342	High performance low-bandgap (0.8 eV) single junction GaInNAsSb solar cells incorporating Au-based back surface reflectors. *Solar Energy Materials and Solar Cells*, **2022**, 234, 111413	6.4	0
341	Use of Nanostructured Alumina Thin Films in Multilayer Anti-Reflective Coatings. *Nanotechnology*, **2021**,	3.4	2
340	Wide spectral coverage (0.7–2.2 eV) lattice-matched multijunction solar cells based on AlGaInP, AlGaAs and GaInNAsSb materials. *Progress in Photovoltaics: Research and Applications*, **2021**, 29, 869	6.8	1
339	Hybrid quasi-3D optimization of grid architecture for single junction photovoltaic converters. *Optical and Quantum Electronics*, **2021**, 53, 205	2.4	
338	REAP: revealing drug tolerant persister cells in cancer using contrast enhanced optical coherence and photoacoustic tomography. *JPhys Photonics*, **2021**, 3, 021001	2.5	1
337	Sub-50 fs pulse generation from a SESAM mode-locked Tm,Ho-codoped calcium aluminate laser. *Optics Letters*, **2021**, 46, 2642-2645	3	4
336	Quantum dot membrane external-cavity surface-emitting laser at 1.5 μm. *Applied Physics Letters*, **2021**, 118, 231101	3.4	1
335	Watt-level blue light for precision spectroscopy, laser cooling and trapping of strontium and cadmium atoms. *Optics Express*, **2021**, 29, 25462-25476	3.3	2
334	Time-Resolved Raman Spectrometer With High Fluorescence Rejection Based on a CMOS SPAD Line Sensor and a 573-nm Pulsed Laser. *IEEE Transactions on Instrumentation and Measurement*, **2021**, 70, 1-10	5.2	3
333	GaAs surface passivation for InAs/GaAs quantum dot based nanophotonic devices. *Nanotechnology*, **2021**, 32, 130001	3.4	2
332	Nonselective etching of As and P based III-V solar cell heterostructures with aqueous solutions of HIO3 and HCl. *Solar Energy Materials and Solar Cells*, **2021**, 226, 111097	6.4	1
331	VECSELs in the Wavelength Range 1.18–1.55 μm **2021**, 27-62		
330	InGaN-diode-pumped AlGaInP VECSEL with sub-kHz linewidth at 689 nm. *Optics Express*, **2021**, 29, 3258-3268	3.3	1
329	High power 739 nm VECSELs for future Yb ion cooling. *Applied Optics*, **2021**, 60, 676-680	1.7	0

328	High-Power 760 nm VECSEL Based on Quantum Dot Gain Mirror. *IEEE Journal of Quantum Electronics*, **2020**, 56, 1-4	2	4
327	Raman spectroscopy of GaSb1−xBix alloys with high Bi content. *Applied Physics Letters*, **2020**, 116, 202103	3.4	4
326	Comparative Analysis of Injection Microdisk Lasers Based on InGaAsN Quantum Wells and InAs/InGaAs Quantum Dots. *Semiconductors*, **2020**, 54, 263-267	0.7	2
325	Circular Dichroism in the Second Harmonic Field Evidenced by Asymmetric Au Coated GaAs Nanowires. *Micromachines*, **2020**, 11,	3.3	4
324	Zinc-indiffused MgO:PPLN waveguides for blue/UV generation via VECSEL pumping. *Applied Optics*, **2020**, 59, 4921-4926	1.7	1
323	SESAM mode-locked Tm:LuYO ceramic laser generating 54-fs pulses at 2048 nm. *Applied Optics*, **2020**, 59, 10493-10497	1.7	15
322	Power scaling and thermal lensing in 825 nm emitting membrane external-cavity surface-emitting lasers. *Optics Letters*, **2020**, 45, 547	3	8
321	Precise length definition of active GaAs-based optoelectronic devices for low-loss silicon photonics integration. *Optics Letters*, **2020**, 45, 943-946	3	1
320	Thin-film InAs/GaAs quantum dot solar cell with planar and pyramidal back reflectors. *Applied Optics*, **2020**, 59, 6304-6308	1.7	2
319	Quantum Dot-Based Thin-Film III-V Solar Cells. *Lecture Notes in Nanoscale Science and Technology*, **2020**, 1-48	0.3	0
318	Edge-enhanced optical parametric generation in periodically poled LiNbO. *Optics Express*, **2020**, 28, 20879-20887	3.5	3
317	The role of As species in self-catalyzed growth of GaAs and GaAsSb nanowires. *Nanotechnology*, **2020**, 31, 465601	3.4	2
316	Power loss mechanisms in n-type modulation-doped AlGaAs/GaAsBi quantum well heterostructures. *Semiconductor Science and Technology*, **2020**, 35, 095038	1.8	1
315	Electronic transport in n-type modulation-doped AlGaAs/GaAsBi quantum well structures: influence of Bi and thermal annealing on electron effective mass and electron mobility. *Semiconductor Science and Technology*, **2020**, 35, 025009	1.8	2
314	High-Power 1.5 μm Tapered Distributed Bragg Reflector Laser Diodes for Eye-Safe LIDAR. *IEEE Photonics Technology Letters*, **2020**, 32, 1249-1252	2.2	2
313	GaSb diode lasers tunable around 2.6 μm using silicon photonics resonators or external diffractive gratings. *Applied Physics Letters*, **2020**, 116, 081105	3.4	4
312	High power GaInNAs superluminescent diodes emitting over 400 mW in the 1.2 μm wavelength range. *Applied Physics Letters*, **2019**, 115, 081104	3.4	4
311	Impact of Bi incorporation on the evolution of microstructure during growth of low-temperature GaAs:Bi/Ga(As,Bi) layers. *Journal of Applied Physics*, **2019**, 126, 085305	2.5	4

310	Polarization Responses of a Solitary and Optically Injected Vertical Cavity Spin Laser. *IEEE Journal of Quantum Electronics*, **2019**, 55, 1-9	2	6
309	Analysis of GaAsBi growth regimes in high resolution with respect to As/Ga ratio using stationary MBE growth. *Journal of Crystal Growth*, **2019**, 511, 33-41	1.6	9
308	Gradients of Be-dopant concentration in self-catalyzed GaAs nanowires. *Nanotechnology*, **2019**, 30, 335709	3.4	4
307	Epitaxial phases of high Bi content GaSbBi alloys. *Journal of Crystal Growth*, **2019**, 516, 67-71	1.6	3
306	Photovoltaic properties of low-bandgap (0.7–0.9 eV) lattice-matched GaInNAsSb solar junctions grown by molecular beam epitaxy on GaAs. *Solar Energy Materials and Solar Cells*, **2019**, 195, 198-203	6.4	8
305	GaInAsSb/AlGa(In)AsSb type I quantum wells emitting in 3 μm range for application in superluminescent diodes. *Optical Materials*, **2019**, 91, 274-278	3.3	1
304	Thermophotonic cooling in GaAs based light emitters. *Applied Physics Letters*, **2019**, 114, 051101	3.4	11
303	AlGaAs/AlGaInP VECSELs With Direct Emission at 740–770 nm. *IEEE Photonics Technology Letters*, **2019**, 31, 1245-1248	2.2	8
302	Flip-Chip Wafer-Fused OP-VECSELs Emitting 3.65 W at the 1.55-μm Waveband. *IEEE Journal of Selected Topics in Quantum Electronics*, **2019**, 25, 1-5	3.8	4
301	InAs/InP quantum dot VECSEL emitting at 1.5 μm. *Applied Physics Letters*, **2019**, 115, 171105	3.4	9
300	High Power $1.5mu$ m Pulsed Laser Diode With Asymmetric Waveguide and Active Layer Near p-cladding. *IEEE Photonics Technology Letters*, **2019**, 31, 1635-1638	2.2	8
299	Te incorporation and activation as n-type dopant in self-catalyzed GaAs nanowires. *Physical Review Materials*, **2019**, 3,	3.2	12
298	52-fs SESAM Mode-Locked Tm,Ho:CALGO Laser **2019**,		5
297	Narrow-linewidth operation of folded 1178nm VECSEL with twisted-mode cavity. *Optics Express*, **2019**, 27, 27267-27272	3.3	4
296	Comparison of single-side and double-side pumping of membrane external-cavity surface-emitting lasers. *Optics Letters*, **2019**, 44, 1146-1149	3	10
295	Lasing action in low-resistance nanolasers based on tunnel junctions. *Optics Letters*, **2019**, 44, 3669-3672	3	7
294	Optimization of Ohmic Contacts to p-GaAs Nanowires. *Nanoscale Research Letters*, **2019**, 14, 344	5	1
293	High-power single mode GaSb-based 2 μm superluminescent diode with double-pass gain. *Applied Physics Letters*, **2019**, 115, 231106	3.4	3

292	V-groove etched 1-eV-GaInNAs nipi solar cell. *Applied Physics A: Materials Science and Processing*, **2019**, 125, 1	2.6	5
291	Treatment of telangiectasia on the cheeks with a compact yellow (585 nm) semiconductor laser and a green (532 nm) KTP laser: a randomized double-blinded split-face trial. *Lasers in Surgery and Medicine*, **2019**, 51, 223-229	3.6	5
290	VECSEL-Based 590-nm Laser System With 8 W of Output Power for the Treatment of Vascular Lesions. *IEEE Journal of Selected Topics in Quantum Electronics*, **2019**, 25, 1-8	3.8	10
289	Lattice-matched four-junction tandem solar cell including two dilute nitride bottom junctions. *Progress in Photovoltaics: Research and Applications*, **2019**, 27, 299-305	6.8	10
288	Deterministic Switching of the Growth Direction of Self-Catalyzed GaAs Nanowires. *Nano Letters*, **2019**, 19, 82-89	11.5	11
287	Sub-100 ps Monolithic Diamond Raman Laser Emitting at 573 nm. *IEEE Photonics Technology Letters* , **2018**, 30, 981-984	2.2	6
286	Resonant Absorption in GaAs-Based Nanowires by Means of Photo-Acoustic Spectroscopy. *International Journal of Thermophysics*, **2018**, 39, 1	2.1	11
285	A study of electric transport in n- and p-type modulation-doped GaInNAs/GaAs quantum well structures under a high electric field. *Semiconductor Science and Technology*, **2018**, 33, 064003	1.8	2
284	Dilute nitride triple junction solar cells for space applications: Progress towards highest AM0 efficiency. *Progress in Photovoltaics: Research and Applications*, **2018**, 26, 740-744	6.8	11
283	GaSb superluminescent diodes with broadband emission at 2.55 □m. *Applied Physics Letters*, **2018**, 112, 051106	3.4	10
282	Light-trapping enhanced thin-film III-V quantum dot solar cells fabricated by epitaxial lift-off. *Solar Energy Materials and Solar Cells*, **2018**, 181, 83-92	6.4	13
281	Optical properties of n- and p-type modulation doped GaAsBi/AlGaAs quantum well structures. *Journal of Alloys and Compounds*, **2018**, 739, 987-996	5.7	9
280	Fiber Lasers of Prof. Okhotnikov: Review of the Main Achievements and Breakthrough Technologies. *IEEE Journal of Selected Topics in Quantum Electronics*, **2018**, 24, 1-14	3.8	3
279	Wet etching of dilute nitride GaInNAs, GaInNAsSb, and GaNAsSb alloys lattice-matched to GaAs. *Corrosion Science*, **2018**, 136, 268-274	6.8	2
278	Photo-Acoustic Spectroscopy Reveals Extrinsic Optical Chirality in GaAs-Based Nanowires Partially Covered with Gold. *International Journal of Thermophysics*, **2018**, 39, 1	2.1	13
277	Ho:KY(WO) thin-disk laser passively Q-switched by a GaSb-based SESAM. *Optics Express*, **2018**, 26, 9011-9016	3.3	5
276	Sub-10 optical-cycle passively mode-locked Tm:(LuSc)O ceramic laser at 2 □m. *Optics Express*, **2018**, 26, 10299-10304	3.3	34
275	AlGaAs-based vertical-external-cavity surface-emitting laser exceeding 4 W of direct emission power in the 740-790 nm spectral range. *Optics Letters*, **2018**, 43, 1578-1581	3	8

274	1.34 Îm VECSEL mode-locked with a GaSb-based SESAM. *Optics Letters*, **2018**, 43, 3353-3356	3	10
273	Comparison of metal/polymer back reflectors with half-sphere, blazed, and pyramid gratings for light trapping in III-V solar cells. *Optics Express*, **2018**, 26, A331-A340	3.3	10
272	Low loss GaInNAs/GaAs gain waveguides with U-bend geometry for single-facet coupling in hybrid photonic integration. *Applied Physics Letters*, **2018**, 113, 041104	3.4	4
271	Site-Controlled Epitaxy of InAs Quantum Dots on Nanoimprint Lithography Patterns **2018**, 277-292		1
270	87 fs mode-locked Tm,Ho:CaYAlO laser at ~2043 nm. *Optics Letters*, **2018**, 43, 915-918	3	27
269	Exciton localization and structural disorder of GaAs1−xBix/GaAs quantum wells grown by molecular beam epitaxy on (311)B GaAs substrates. *Semiconductor Science and Technology*, **2018**, 33, 084002	1.8	4
268	72-W vertical-external-cavity surface-emitting laser with 1180-nm emission for laser guide star adaptive optics. *Electronics Letters*, **2018**, 54, 1135-1137	1.1	8
267	Surface doping of GaxIn1−xAs semiconductor crystals with magnesium. *Materialia*, **2018**, 2, 33-36	3.2	
266	Integrated multi-wavelength mid-IR light source for gas sensing **2018**,		4
265	Cascaded crystalline Raman lasers for extended wavelength coverage: continuous-wave, third-Stokes operation. *Optica*, **2018**, 5, 1406	8.6	13
264	Improved Light Trapping in Quantum Dot Solar Cells Using Double-sided Nanostructuring **2018**,		2
263	Data transmission at 1300 nm using optical interposer comprising hybrid integrated silicon waveguide and dilute nitride electroabsorption modulator. *Optics Express*, **2018**, 26, 34336-34345	3.3	2
262	Room temperature lasing in injection microdisks with InGaAsN/GaAs quantum well active region. *Journal of Physics: Conference Series*, **2018**, 1124, 081048	0.3	1
261	High-Power 1.5- mu m Broad Area Laser Diodes Wavelength Stabilized by Surface Gratings. *IEEE Photonics Technology Letters*, **2018**, 30, 1870-1873	2.2	4
260	Oxidation-Induced Changes in the ALD-AlO/InAs(100) Interface and Control of the Changes for Device Processing. *ACS Applied Materials & Interfaces*, **2018**, 10, 44932-44940	9.5	6
259	Optical properties of GaAs1−xBix/GaAs quantum well structures grown by molecular beam epitaxy on (100) and (311)B GaAs substrates. *Semiconductor Science and Technology*, **2018**, 33, 124015	1.8	3
258	Molecular Beam Epitaxy of Dilute Nitride Optoelectronic Devices **2018**, 73-94		1
257	Near-threshold high spin amplification in a 1300 nm GaInNAs spin laser. *Semiconductor Science and Technology*, **2018**, 33, 094005	1.8	3

256	Evidence of Optical Circular Dichroism in GaAs-Based Nanowires Partially Covered with Gold. *Advanced Optical Materials*, **2017**, 5, 1601063	8.1	25
255	31% European InGaP/GaAs/InGaAs Solar Cells for Space Application. *E3S Web of Conferences*, **2017**, 16, 03003	0.5	8
254	Intracavity double diode structures with GaInP barrier layers for thermophotonic cooling **2017**,		1
253	Structural Investigation of Uniform Ensembles of Self-Catalyzed GaAs Nanowires Fabricated by a Lithography-Free Technique. *Nanoscale Research Letters*, **2017**, 12, 192	5	18
252	Multi-wavelength mid-IR light source for gas sensing **2017**,		3
251	Diode-pumped mode-locked Tm:LuAG laser at 2 μm based on GaSb-SESAM. *Optics Letters*, **2017**, 42, 839-842	3	23
250	Back grating optimization for light trapping in thin-film quantum dot solar cells **2017**,		3
249	Sub-10 optical-cycle mode-locked Tm:(Lu2/3Sc1/3)2O3 mixed ceramic laser at 2057 nm **2017**,		1
248	Field Emission from Self-Catalyzed GaAs Nanowires. *Nanomaterials*, **2017**, 7,	5.4	29
247	Optically pumped VECSELs: review of technology and progress. *Journal Physics D: Applied Physics*, **2017**, 50, 383001	3	86
246	Generation of Sub-100 ps Pulses at 532, 355, and 266 nm Using a SESAM Q-Switched Microchip Laser. *IEEE Photonics Technology Letters*, **2017**, 29, 1816-1819	2.2	6
245	Decreasing Defect-State Density of Al2O3/GaxIn1−xAs Device Interfaces with InOx Structures. *Advanced Materials Interfaces*, **2017**, 4, 1700722	4.6	4
244	Sub-Poissonian Narrowing of Length Distributions Realized in Ga-Catalyzed GaAs Nanowires. *Nano Letters*, **2017**, 17, 5350-5355	11.5	31
243	Novel Concepts for High-Efficiency Lightweight Space Solar Cells. *E3S Web of Conferences*, **2017**, 16, 03007	0.5	4
242	Performace of Dilute Nitride Triple Junction Space Solar Cell Grown by MBE. *E3S Web of Conferences*, **2017**, 16, 03008	0.5	2
241	Photo-acoustic spectroscopy revealing resonant absorption of self-assembled GaAs-based nanowires. *Scientific Reports*, **2017**, 7, 2833	4.9	24
240	. *IEEE Photonics Technology Letters*, **2017**, 29, 114-117	2.2	13
239	Polarization resolved photoluminescence in GaAs1−xBix/GaAs quantum wells. *Journal of Luminescence*, **2017**, 182, 49-52	3.8	6

238	Local variation in Bi crystal sites of epitaxial GaAsBi studied by photoelectron spectroscopy and first-principles calculations. *Applied Surface Science*, **2017**, 396, 688-694	6.7	5
237	High-power 1550 nm tapered DBR laser diodes for LIDAR applications **2017**,		5
236	High-Power 1180-nm GaInNAs DBR Laser Diodes. *IEEE Photonics Technology Letters*, **2017**, 29, 2023-2026	2.2	5
235	33 W continuous output power semiconductor disk laser emitting at 1275 nm. *Optics Express*, **2017**, 25, 7008-7013	3.3	7
234	Thulium doped LuAG ceramics for passively mode locked lasers. *Optics Express*, **2017**, 25, 7084-7091	3.3	12
233	Diode-pumped Tm:KY(WO) laser passively modelocked with a GaSb-SESAM. *Optics Express*, **2017**, 25, 25760-25766	3.3	6
232	1.4 μm continuous-wave diamond Raman laser. *Optics Express*, **2017**, 25, 31377-31383	3.3	10
231	Sub-50 ps pulses at 620 nm obtained from frequency doubled 1240 nm diamond Raman laser. *Optics Express*, **2017**, 25, 30365-30370	3.3	6
230	The Role of Epitaxial Strain on the Spontaneous Formation of Bi-Rich Nanostructures in Ga(As,Bi) Epilayers and Quantum Wells. *Nanoscience and Nanotechnology Letters*, **2017**, 9, 1132-1138	0.8	5
229	Passively Mode-Locked Tm:LuAG Ceramic Laser **2017**,		1
228	Optical Energy Transfer and Loss Mechanisms in Coupled Intracavity Light Emitters. *IEEE Transactions on Electron Devices*, **2016**, 63, 3567-3573	2.9	19
227	Electrical switching of photoluminescence of single site-controlled InAs quantum dots. *Electronics Letters*, **2016**, 52, 1240-1242	1.1	
226	Enhancement of photocurrent in GaInNAs solar cells using Ag/Cu double-layer back reflector. *Applied Physics Letters*, **2016**, 109, 251104	3.4	6
225	Single-frequency 571nm VECSEL for photo-ionization of magnesium **2016**,		1
224	High Spectral Purity High-Power GaSb-Based DFB Laser Fabricated by Nanoimprint Lithography. *IEEE Photonics Technology Letters*, **2016**, 28, 1233-1236	2.2	11
223	Influence of As/group-III flux ratio on defects formation and photovoltaic performance of GaInNAs solar cells. *Solar Energy Materials and Solar Cells*, **2016**, 149, 213-220	6.4	26
222	High-power temperature-stable GaInNAs distributed Bragg reflector laser emitting at 1180 nm. *Optics Letters*, **2016**, 41, 657-60	3	11
221	Effects of insertion of strain-engineering Ga(In)NAs layers on optical properties of InAs/GaAs quantum dots for high-efficiency solar cells. *Optical Materials*, **2016**, 52, 177-180	3.3	4

220	Determination of composition and energy gaps of GaInNAsSb layers grown by MBE. *Journal of Crystal Growth*, **2016**, 438, 49-54	1.6	12
219	Nanostructures for light management in thin-film GaAs quantum dot solar cells **2016**,		3
218	Frequency-doubled passively Q-switched microchip laser producing 225 ps pulses at 671 nm. *Optics Letters*, **2016**, 41, 5385-5388	3	3
217	VECSEL systems for the generation and manipulation of trapped magnesium ions. *Optica*, **2016**, 3, 1294	8.6	10
216	High-efficiency GaInP/GaAs/GaInNAs solar cells grown by combined MBE-MOCVD technique. *Progress in Photovoltaics: Research and Applications*, **2016**, 24, 914-919	6.8	26
215	High power (60 mW) GaSb-based 1.9 μm superluminescent diode with cavity suppression element. *Applied Physics Letters*, **2016**, 109, 231102	3.4	13
214	Compact microdisk cavity laser with GaInNAs/GaAs quantum well. *Journal of Physics: Conference Series*, **2016**, 741, 012110	0.3	
213	Comparative study of defect levels in GaInNAs, GaNAsSb, and GaInNAsSb for high-efficiency solar cells. *Applied Physics Letters*, **2016**, 108, 122104	3.4	11
212	Microdisk lasers based on GaInNAs(Sb)/GaAs(N) quantum wells. *Journal of Applied Physics*, **2016**, 120, 233103	2.5	6
211	SESAM mode-locked Tm:CALGO laser at 2 μm. *Optical Materials Express*, **2016**, 6, 131	2.6	40
210	InGaAs-QW VECSEL emitting >1.300-nm via intracavity Raman conversion **2016**,		3
209	Site-controlled InAs quantum dot chains coupled to surface plasmons. *Optica*, **2016**, 3, 139	8.6	2
208	Spontaneous formation of three-dimensionally ordered Bi-rich nanostructures within GaAs1-x Bi x /GaAs quantum wells. *Nanotechnology*, **2016**, 27, 325603	3.4	27
207	Broadly tunable mode-locked Ho:YAG ceramic laser around 2.1 μm. *Optics Express*, **2016**, 24, 18003-12	3.3	23
206	Lithography-free oxide patterns as templates for self-catalyzed growth of highly uniform GaAs nanowires on Si(111). *Nanotechnology*, **2015**, 26, 275301	3.4	27
205	Spontaneous formation of nanostructures by surface spinodal decomposition in GaAs1−xBix epilayers. *Journal of Applied Physics*, **2015**, 117, 185302	2.5	25
204	Microchip laser Q-switched with GaInNAs/GaAs SESAM emitting 204 ps pulses at 1342 nm. *Electronics Letters*, **2015**, 51, 850-852	1.1	2
203	GaSb-based SESAM mode-locked Tm:YAG ceramic laser at 2 μm. *Optics Express*, **2015**, 23, 1361-9	3.3	40

202	615 nm GaInNAs VECSEL with output power above 10 W. *Optics Express*, **2015**, 23, 20280-7	3.3	12
201	The Role of Groove Periodicity in the Formation of Site-Controlled Quantum Dot Chains. *Nanoscale Research Letters*, **2015**, 10, 938	5	3
200	Effects of thinning and heating for TiO2/AlInP junctions. *Journal of Electron Spectroscopy and Related Phenomena*, **2015**, 205, 6-9	1.7	
199	1180nm VECSEL with 50 W output power **2015**,		4
198	Oxidation of the GaAs semiconductor at the Al2O3/GaAs junction. *Physical Chemistry Chemical Physics*, **2015**, 17, 7060-6	3.6	11
197	High-gain 1.3 μm GaInNAs semiconductor optical amplifier with enhanced temperature stability for all-optical signal processing at 10 Gb/s. *Applied Optics*, **2015**, 54, 46-52	1.7	8
196	Te-doping of self-catalyzed GaAs nanowires. *Applied Physics Letters*, **2015**, 107, 012101	3.4	21
195	Temperature coefficients for GaInP/GaAs/GaInNAsSb solar cells **2015**,		12
194	Detecting lateral composition modulation in dilute Ga(As,Bi) epilayers. *Nanotechnology*, **2015**, 26, 425701	3.4	15
193	Monolithic GaInNAsSb/GaAs VECSEL Operating at 1550 nm. *IEEE Journal of Selected Topics in Quantum Electronics*, **2015**, 21, 480-484	3.8	15
192	Mode-locked Tm,Ho:KLu(WO(4))(2) laser at 2060 nm using InGaSb-based SESAMs. *Optics Express*, **2015**, 23, 4614-9	3.3	17
191	. *IEEE Photonics Technology Letters*, **2015**, 27, 1691-1694	2.2	1
190	Negative and positive magnetoresistance in GaInNAs/GaAs modulation-doped quantum well structures. *Applied Physics A: Materials Science and Processing*, **2015**, 118, 823-829	2.6	3
189	Circular polarization switching and bistability in an optically injected 1300 nm spin-vertical cavity surface emitting laser. *Applied Physics Letters*, **2015**, 106, 021117	3.4	23
188	Performance assessment of multijunction solar cells incorporating GaInNAsSb. *Nanoscale Research Letters*, **2014**, 9, 61	5	28
187	Optical gain in 1.3-μm electrically driven dilute nitride VCSOAs. *Nanoscale Research Letters*, **2014**, 9, 22	5	2
186	Dynamics of time-resolved photoluminescence in GaInNAs and GaNAsSb solar cells. *Nanoscale Research Letters*, **2014**, 9, 80	5	20
185	Identification of an isolated arsenic antisite defect in GaAsBi. *Applied Physics Letters*, **2014**, 104, 052110	3.4	16

184	High quality InP nanopyramidal frusta on Si. *CrystEngComm*, **2014**, 16, 4624-4632	3.3	4
183	Optically Pumped Edge-Emitting GaAs-Based Laser With Direct Orange Emission. *IEEE Photonics Technology Letters*, **2014**, 26, 384-386	2.2	13
182	Magnetotransport study on as-grown and annealed n- and p-type modulation-doped GaInNAs/GaAs strained quantum well structures. *Nanoscale Research Letters*, **2014**, 9, 141	5	13
181	Analytic modeling of temperature dependence of 2D carrier mobility in as-grown and annealed GaInNAs/GaAs quantum well structures. *Semiconductor Science and Technology*, **2014**, 29, 125009	1.8	11
180	Formation and phase transformation of Bi-containing QD-like clusters in annealed GaAsBi. *Nanotechnology*, **2014**, 25, 205605	3.4	39
179	Absorption recovery dynamics in 2μm GaSb-based SESAMs. *Journal Physics D: Applied Physics*, **2014**, 47, 065102	3	18
178	Instability of structural defects generated by electron irradiation in GaInNAs quantum wells. *Journal of Luminescence*, **2014**, 154, 584-586	3.8	3
177	Pulsed high-power yellow-orange VECSEL **2014**,		1
176	Incorporation model of N into GaInNAs alloys grown by radio-frequency plasma-assisted molecular beam epitaxy. *Journal of Applied Physics*, **2014**, 116, 213101	2.5	9
175	Ultrahigh precision nonlinear reflectivity measurement system for saturable absorber mirrors with self-referenced fluence characterization. *Optics Letters*, **2014**, 39, 4384-7	3	5
174	High-efficiency 20 W yellow VECSEL. *Optics Express*, **2014**, 22, 6372-80	3.3	60
173	Observation of atomic ordering of triple-period-A and -B type in GaAsBi. *Applied Physics Letters*, **2014**, 105, 041602	3.4	31
172	Cavity-enhanced single photon emission from site-controlled In(Ga)As quantum dots fabricated using nanoimprint lithography. *Applied Physics Letters*, **2014**, 104, 213104	3.4	7
171	Control of emitted light polarization in a 1310 nm dilute nitride spin-vertical cavity surface emitting laser subject to circularly polarized optical injection. *Applied Physics Letters*, **2014**, 105, 181106	3.4	13
170	Unveiling and controlling the electronic structure of oxidized semiconductor surfaces: Crystalline oxidized InSb(100)(1 □2)-O. *Physical Review B*, **2014**, 90,	3.3	10
169	SESAM mode-locked red praseodymium laser. *Optics Letters*, **2014**, 39, 6939-41	3	40
168	Synthesis and Characterization of Layered Tin Monoxide Thin Films with Monocrystalline Structure on III□V Compound Semiconductor. *Advanced Materials Interfaces*, **2014**, 1, 1300022	4.6	1
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